# Buffer with Open Drain Output

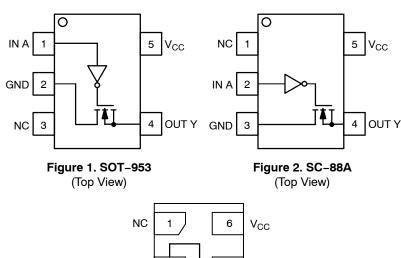
# NL17SG07

The NL17SG07 MiniGate<sup>™</sup> is an advanced high-speed CMOS Buffer with Open Drain Output in ultra-small footprint.

The NL17SG07 input structures provides protection when voltages up to 5.5 V are applied with  $V_{CC}$  greater than or equal to 0.9 volts, otherwise the protection is up to 4.6 volts regardless of the supply voltage.

# Features

- Wide Operating  $V_{CC}$  Range: 0.9 V to 3.6 V
- High Speed:  $t_{PD}$  = 2.5 ns (Typ) at  $V_{CC}$  = 3.0 V,  $C_L$  = 15 pF
- Low Power Dissipation:  $I_{CC} = 0.5 \ \mu A \ (Max)$  at  $T_A = 25^{\circ}C$
- 5.5 V Overvoltage Tolerant (OVT) Input Pins ( $V_{CC} \ge 0.9 \text{ V}$ )
- Ultra-Small Packages
- These are Pb-Free and Halide-Free Devices



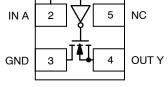






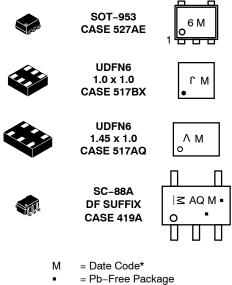
Figure 4. Logic Symbol



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## MARKING DIAGRAMS



(Note: Microdot may be in either location)

\*Date Code orientation and/or position may vary depending upon manufacturing location.

#### **PIN ASSIGNMENT**

PIN	SOT-953	SC-88A	UDFN6
1	IN A	NC	NC
2	GND	IN A	IN A
3	NC	GND	GND
4	OUT Y	OUT Y	OUT Y
5	V <sub>CC</sub>	V <sub>CC</sub>	NC
6	-	-	V <sub>CC</sub>

## FUNCTION TABLE

Input A	Output Y
L	L
Н	Z

## **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

# **MAXIMUM RATINGS**

Symbol	Parameter		Value	Unit
V <sub>CC</sub>	DC Supply Voltage		–0.5 to +5.5	V
V <sub>IN</sub>	DC Input Voltage	$\begin{array}{l} V_{CC} \geq 0.9 \ V \\ V_{CC} < 0.9 \ V \end{array}$	-0.5 to +5.5 -0.5 to +4.6	V
V <sub>OUT</sub>	DC Output Voltage		–0.5 to V <sub>CC</sub> + 0.5	V
Ι <sub>ΙΚ</sub>	DC Input Diode Current	V <sub>IN</sub> < GND	-20	mA
I <sub>OK</sub>	DC Output Diode Current	V <sub>OUT</sub> < GND	-20	mA
I <sub>OUT</sub>	DC Output Source/Sink Current		±20	mA
I <sub>CC</sub>	DC Supply Current per Supply Pin		±20	mA
I <sub>GND</sub>	DC Ground Current per Ground Pin		±20	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
TJ	Junction Temperature Under Bias		+150	°C
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
$V_{\text{ESD}}$	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3)	>2000 >100	V
I <sub>LATCHUP</sub>	Latch-up Performance above $V_{CC}$ and below GND at 12 $$	25°C (Note 4)	±75	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.

Tested to EIA/JESD22–A114–A.
Tested to EIA/JESD22–A115–A.

4. Tested to EIA/JESD78.

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Characteristics	Min	Max	Unit
V <sub>CC</sub>	Positive DC Supply Voltage	0.9	3.6	V
V <sub>IN</sub>	Digital Input Voltage	0.0	3.6	V
V <sub>OUT</sub>	Output Voltage Output at High or Low Tri–State Mode (N Power–Down Mode (V <sub>CC</sub> :	ote 5) 0.0	V <sub>CC</sub> 3.6 3.6	V
T <sub>A</sub>	Operating Temperature Range	-55	+125	°C
$\Delta t$ / $\Delta V$	Input Transition Rise or Fail Rate $V_{CC}$ = 3.3 V ±	0.3 V 0	10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability. 5. Applicable to devices with outputs that may be tri-stated.

# DC ELECTRICAL CHARACTERISTICS

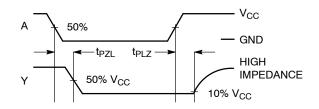
				Vcc		T <sub>A</sub> = 25°C		–55°C ≤ T	A ≤ 125°C	
Symbol	Parameter	с	ondition	(V)	Min	Тур	Max	Min	Max	Unit
VIH	High-Level			0.9	V <sub>CC</sub>			V <sub>CC</sub>		
	Input Voltage			1.1 to 1.3	0.70 x V <sub>CC</sub>			0.70 x V <sub>CC</sub>		
				1.4 to 1.6	0.65 x V <sub>CC</sub>			0.65 x V <sub>CC</sub>		
				1.65 to 1.95	0.65 x V <sub>CC</sub>			0.65 x V <sub>CC</sub>		
				2.3 to 2.7	1.7			1.7		
				3.0 to 3.6	2.0			2.0		1
VIL	Low-Level			0.9			GND		GND	
	Input Voltage			1.1 to 1.3			0.30 x V <sub>CC</sub>		0.30 x V <sub>CC</sub>	]
				1.4 to 1.6			0.35 x V <sub>CC</sub>		0.35 x V <sub>CC</sub>	v
				1.65 to 1.95			0.35 x V <sub>CC</sub>		0.35 x V <sub>CC</sub>	]
				2.3 to 2.7			0.7		0.7	1
				3.0 to 3.6			0.8		0.8	
V <sub>OL</sub>	Low-Level Output Voltage	V <sub>IN</sub> =	I <sub>OL</sub> = 20 μA	0.9			0.1		0.1	V
	Oulput voltage	V <sub>IH</sub> or V <sub>IL</sub>	l <sub>OL</sub> = 0.3 mA	1.1 to 1.3			0.25 x V <sub>CC</sub>		0.25 x V <sub>CC</sub>	
			l <sub>OL</sub> = 1.7 mA	1.4 to 1.6			0.25 x V <sub>CC</sub>		0.25 x V <sub>CC</sub>	
			I <sub>OL</sub> = 3.0 mA	1.65 to 1.95			0.45		0.45	1
			I <sub>OL</sub> = 4.0 mA	2.3 to 2.7			0.4		0.4	1
			I <sub>OL</sub> = 8.0 mA	3.0 to 3.6			0.4		0.4	1
I <sub>IN</sub>	Input Leakage Current	0 ≤	V <sub>IN</sub> ≤ 3.6 V	0 to 3.6			±0.1		±1.0	μΑ
I <sub>CC</sub>	Quiescent Supply Current	V <sub>IN</sub> =	V <sub>CC</sub> or GND	3.6			0.5		10	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

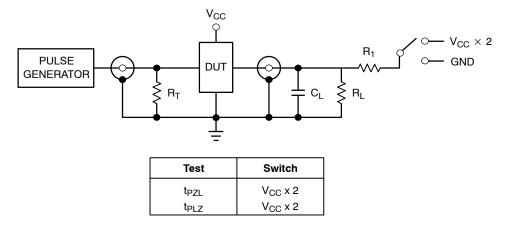
## AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$ )

					T <sub>A</sub> = 25°C	;	T <sub>A</sub> −55°C to	= 0 +125°C	
Symbol	Parameter	Test Condition	V <sub>CC</sub> (V)	Min	Тур	Max	Min	Max	Uni
t <sub>PZL</sub>	Propagation Delay,	C <sub>L</sub> = 10 pF,	0.9	-	12	-	-	-	ns
	Enable Time, A to Y	$R_1 = R_L = 5 k\Omega$	1.1 to 1.3	-	5.5	6.8	-	8.8	
	A lo f		1.4 to 1.6	-	4.0	5.7	-	7.3	
			1.65 to 1.95	_	3.3	3.9	-	5.9	
			2.3 to 2.7	-	2.7	3.3	-	4.5	1
			3.0 to 3.6	-	2.4	2.9	-	3.7	
		C <sub>L</sub> = 15 pF,	0.9	-	12.5	-	-	-	ns
		$R_1 = R_L = 5 k\Omega$	1.1 to 1.3	-	5.8	7.0	-	9.0	
			1.4 to 1.6	-	4.1	6.0	-	7.4	
			1.65 to 1.95	_	3.4	4.0	-	6.2	
			2.3 to 2.7	_	2.8	3.4	-	4.6	
			3.0 to 3.6	_	2.5	3.0	-	3.7	
		C <sub>L</sub> = 30 pF,	0.9	-	13.2	-	-	-	n
		$R_1 = R_L = 5 k\Omega$	1.1 to 1.3	-	6.2	7.4	-	9.4	
			1.4 to 1.6	-	4.5	6.2	-	7.6	
			1.65 to 1.95	-	3.5	4.2	-	6.4	
			2.3 to 2.7	-	3.0	3.6	_	4.7	
			3.0 to 3.6	-	2.6	3.1	-	3.9	
t <sub>PLZ</sub>	Propagation Delay,	C <sub>L</sub> = 10 pF,	0.9	-	8.0	-	-	-	ns
	Disable Time,	$R_1 = R_L = 5 k\Omega$	1.1 to 1.3	-	6.5	10.9	-	11.5	
	A to Y		1.4 to 1.6	-	5.2	7.2	-	8.3	
			1.65 to 1.95	-	4.9	7.0	-	7.8	
			2.3 to 2.7	-	3.8	6.5	-	7.3	
			3.0 to 3.6	-	3.5	6.2	_	6.8	
		C <sub>L</sub> = 15 pF,	0.9	_	11.1	-	-	_	n
		$R_1 = R_L = 5 k\Omega$	1.1 to 1.3	-	9.0	13.4	-	14	
			1.4 to 1.6	-	7.9	10	-	10.8	
			1.65 to 1.95	-	7.6	9.5	-	10.5	
			2.3 to 2.7	-	6.3	7.8	-	10	
			3.0 to 3.6	-	6.0	7.2	-	9.3	
		C <sub>L</sub> = 30 pF,	0.9	_	16.2	-	-	-	n
		$R_1 = R_L = 5 k\Omega$	1.1 to 1.3	_	14	18.4	-	20	1
			1.4 to 1.6	_	13	15	_	16	
			1.65 to 1.95	_	12.5	14.5	_	15.8	
			2.3 to 2.7	_	11.2	13.5	_	15.4	1
			3.0 to 3.6	_	11	13.2	_	14.3	
C <sub>IN</sub>	Input Capacitance		0 to 3.6	-	3	-	_	_	p
C <sub>PD</sub>	Power Dissipation Capacitance (Note 6)		0.9 to 3.6	_	4	-	-	_	pl

6.  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$ .  $C_{PD}$  is used to determine the no-load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$ .









# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NL17SG07P5T5G	SOT–953 (Pb–Free)	8000 / Tape & Reel
NL17SG07DFT2G	SC-88A (Pb-Free)	3000 / Tape & Reel
NL17SG07AMUTCG	UDFN6 1.45x1 mm (Pb-Free)	3000 / Tape & Reel
NL17SG07CMUTBG*	UDFN6 1x1 mm (Pb-Free)	3000 / Tape & Reel
NL17SG07MU3TBG*	UDFN6 1x1 mm (Pb-Free)	3000 / Tape & Reel

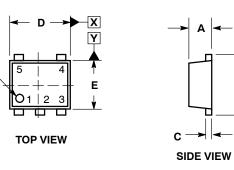
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

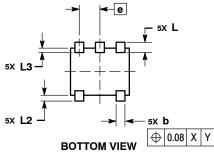
\*In Development

# PACKAGE DIMENSIONS

SOT-953 CASE 527AE ISSUE E

HE

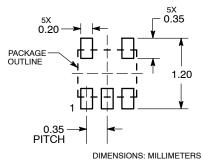




NOTES:
DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
CONTROLLING DIMENSION: MILLIMETERS
MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

I LAO	n, Fhomosions, on d						
	MILLIMETERS						
DIM	MIN	MIN NOM MAX					
Α	0.34	0.37	0.40				
b	0.10	0.15	0.20				
С	0.07	0.12	0.17				
D	0.95	1.00	1.05				
Е	0.75	0.80	0.85				
е		0.35 BS	С				
HE	0.95	1.00	1.05				
L	0.175 REF						
L2	0.05	0.10	0.15				
L3			0.15				

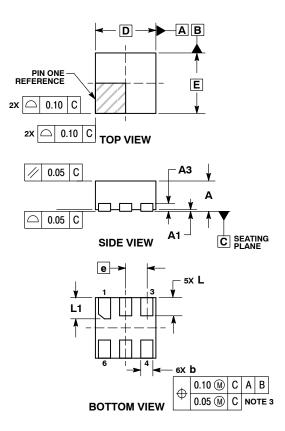
### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# PACKAGE DIMENSIONS

UDFN6 1.0x1.0, 0.35P CASE 517BX ISSUE O

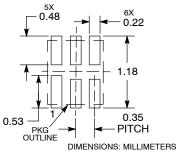


NOTES:

- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. DIMENSION 6 APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP. 4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

	MILLIN	IETERS
DIM	MIN	MAX
Α	0.45	0.55
A1	0.00	0.05
A3	0.13	REF
b	0.12	0.22
D	1.00	BSC
E	1.00	BSC
е	0.35	BSC
L	0.25	0.35
L1	0.30	0.40

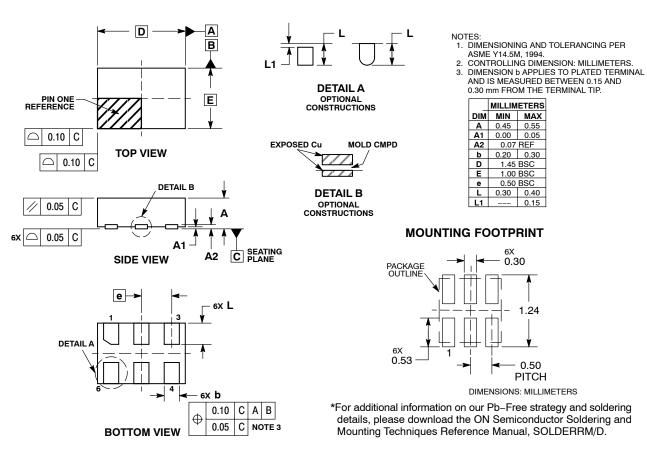
#### RECOMMENDED SOLDERING FOOTPRINT\*



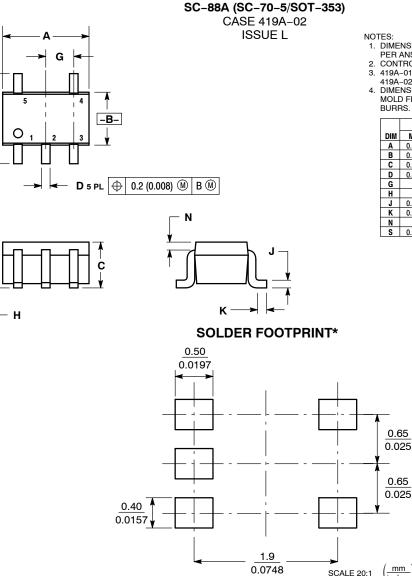
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## PACKAGE DIMENSIONS

UDFN6 1.45x1.0, 0.5P CASE 517AQ ISSUE O



#### PACKAGE DIMENSIONS



0.65

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NL17SG07/D

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

- CONTROLLING DIMENSION: INCH. 419A-01 OBSOLETE. NEW STANDARD
- 419A-02. DIMENSIONS A AND B DO NOT INCLUDE

MOLD FLASH, PROTRUSIONS, OR GATE BURBS

	INC	HES	MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65 BSC	
Н		0.004		0.10
J	0.004	0.010	0.10	0.25
Κ	0.004	0.012	0.10	0.30
Ν	0.008 REF		0.20	REF
S	0.079	0.087	2.00	2.20